

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|--|---|------------------|
| - | 2 | ("6348705").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 08:11 |
| - | 13687 | @ad<=20010508 and 'high dielectric constant' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 08:31 |
| - | 132 | (@ad<=20010508 and 'high dielectric constant') and 'conductive barrier' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/29 14:24 |
| - | 119 | ((@ad<=20010508 and 'high dielectric constant') and 'conductive barrier') and Al | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 08:24 |
| - | 77 | ((@ad<=20010508 and 'high dielectric constant') and 'conductive barrier') and Aluminum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 08:25 |
| - | 3291 | @ad<=20010508 and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 08:33 |
| - | 79 | (@ad<=20010508 and 'BST') and 'TiAlN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/29 13:41 |
| - | 39 | ((@ad<=20010508 and 'BST') and 'TiAlN') and aluminum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 06:54 |
| - | 6626 | ((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 11:37 |
| - | 24 | ((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.) and @ad<=20010508 and 'BST' and 'TiAlN' and 'metal layer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 12:52 |
| - | 29173 | @ad<=20010508 and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 12:05 |
| - | 30 | (@ad<=20010508 and 'ferroelectric') and 'BST' and 'TiAlN' and 'metal layer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/30 07:15 |
| - | 29 | (@ad<=20010508 and 'ferroelectric') and 'BST' and 'TiAlN' and 'aluminum' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 13:26 |
| - | 20 | (@ad<=20010508 and 'ferroelectric') and 'capacitor' with 'BST' and 'TiAlN' and 'aluminum' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/09/16 13:26 |

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| - | 25 | @ad<=20010508 and 'perovskite BST' or 'amorphous BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/16 15:09 |
| - | 3 | @ad<=20010508 and 'amorphous BST' and conductive adj barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 13:06 |
| - | 569 | (257/310).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/16 15:41 |
| - | 532 | ((257/310).CCLS.) and @ad<=20010508 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 13:56 |
| - | 11 | (@ad<=20010508 and 'ferroelectric') and 'BST' and 'barrier' and 'aluminum layer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/09/16 15:45 |
| - | 270 | @ad<=19991222 and 'conductive barrier' and 'TiN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 12:52 |
| - | 566 | ((257/310).CCLS.) and @ad<=20010508 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:05 |
| - | 43 | @ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:05 |
| - | 6 | @ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST' and 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 15:02 |
| - | 2342 | @ad<=19991222 and (257/295-296).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:15 |
| - | 795 | @ad<=19991222 and (257/751).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:09 |
| - | 1232 | @ad<=19991222 and (257/763-764).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:10 |
| - | 372 | @ad<=19991222 and (257/303).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:11 |
| - | 1094 | @ad<=19991222 and (257/306).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:12 |

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| - | 479 | @ad<=19991222 and (438/3).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:12 |
| - | 1072 | @ad<=19991222 and (438/439-440).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:13 |
| - | 687 | @ad<=19991222 and (438/687-688).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:21 |
| - | 4 | (("6294420") or ("6365517")).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:21 |
| - | 38 | @ad<=19991222 and 'high dielectric constant' and 'conductive barrier' and 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 14:26 |
| - | 21 | @ad<=19991222 and 'conductive barrier' and 'TiN' and 'BST' and 'aluminum' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/01/29 15:02 |
| - | 29 | @ad<=19991222 and 'ferroelectric' and 'TiAlN' and 'metal layer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/01 08:54 |
| - | 8 | @ad<=19991222 and 'capacitor' with 'ferroelectric' with 'conductive diffusion barrier' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 14:27 |
| - | 17 | @ad<=19991222 and 'conductive barrier' and 'TiAlN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 12:52 |
| - | 5 | @ad<=19991222 and 'BST' and 'conductive barrier' with 'TiAlN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 13:00 |
| - | 10 | @ad<=19991222 and 'copper' and 'TiAlN' and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 14:42 |
| - | 1 | @ad<=19991222 and 'copper' same 'TiAlN' same 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 13:07 |
| - | 0 | @ad<=19991222 and 'capacitor' with 'BST' with 'TiAlN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 14:25 |
| - | 2 | @ad<=19991222 and 'BST' with 'TiAlN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/05/12 14:25 |

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| - | 8 | @ad<=19991222 and 'capacitor' with 'ferroelectric' with 'conductive diffusion barrier' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:04 |
| - | 0 | @ad<=19991222 and copper near electrode and 'BST' same 'TiAlN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/12 14:39 |
| - | 3 | @ad<=19991222 and copper and 'BST' same 'TiAlN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/12 14:39 |
| - | 50 | @ad<=19991222 and 'Al' and 'TiAlN' and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/12 14:46 |
| - | 25 | @ad<=19991222 and 'Aluminum' and 'TiAlN' and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/02 08:25 |
| - | 48 | @ad<=19991222 and 'conductive' and 'TiAlN' and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/05/12 14:58 |
| - | 15 | @ad<=19991222 and 'stack capacitor' and 'TiAlN' and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:22 |
| - | 2 | "20020167086" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/15 12:55 |
| - | 8 | @ad<=20010508 and 'BST' same 'TiN' same 'aluminum' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:02 |
| - | 3 | @ad<=20010508 and 'high k' same 'TiN' same 'aluminum' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:03 |
| - | 2 | ("5990541").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:03 |
| - | 5 | @ad<=19991222 and 'ferroelectric' same 'barrier' same 'copper' with 'electrode' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:08 |
| - | 236 | @ad<=19991222 and 'ferroelectric' same 'barrier' same 'metal' with 'electrode' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:13 |
| - | 4 | @ad<=19991222 and 'capacitor' same 'ferroelectric' same 'barrier' same 'copper' with 'electrode' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:09 |

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| | 5 | @ad<=19991222 and 'stack capacitor' and 'TiAlN' and 'PZT' and 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:22 |
| | 31 | @ad<=19991222 and 'stack capacitor' and 'TiN' and 'PZT' and 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:29 |
| | 2 | @ad<=19991222 and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:33 |
| | 3 | @ad<=20010508 and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:34 |
| | 283 | @ad<=20010508 and 'capacitor' and 'TiN' and 'PZT' and 'al' with 'electrode' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:35 |
| | 77 | @ad<=20010508 and 'capacitor' same 'electrode' with 'aluminum' same 'barrier' and 'PZT' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 07:40 |
| | 15 | @ad<=20010508 and 'capacitor' same 'electrode' with 'copper' same 'barrier' and 'PZT' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:15 |
| | 3 | @ad<=20010508 and 'electrode' with 'conductive barrier' with 'PZT' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:19 |
| | 55 | @ad<=20010508 and 'electrode' with 'TiN' with 'PZT' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:32 |
| | 81 | @ad<=20010508 and 'electrode' adj2 'copper' with 'TiN' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:33 |
| | 5 | @ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'BST' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:45 |
| | 3 | @ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'high k' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:45 |
| | 66 | @ad<=20010508 and 'copper' with 'electrode' with 'TiN' and 'high dielectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:48 |
| | 3 | @ad<=20010508 and 'copper' adj2 'electrode' with 'TiN' and 'high dielectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/07/01 08:49 |

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| - | 25 | @ad<=19991222 and 'ferroelectric' with 'capacitor' and 'TiAlN' and 'metal layer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/01 11:41 |
| - | 0 | @ad<=19991222 and 'ferroelectric' with 'capacitor' and 'TiAlN' and 'copper electrode' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/01 09:02 |
| - | 1 | "5053917".PN. | USPAT | 2004/07/01 10:37 |
| - | 0 | @ad<=19991222 and 'copper' same 'IrO. ₂ ' same 'Ir. ₀ . _{sub3} ' same 'Ir' and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/01 11:43 |
| - | 4 | @ad<=19991222 and 'copper' same 'IrO. ₂ ' same 'Ir' and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/01 11:43 |
| - | 2 | @ay<=1999 and tang-shaoping.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/01 14:38 |
| - | 6 | @ay<=1999 and summerfelt-scott.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 08:38 |
| - | 4 | @ay<=1999 and crenshaw-darius.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 08:38 |
| - | 1 | @ay<=1999 and kirlin-peter.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 08:41 |
| - | 5 | @ay<=1999 and gnade-bruce.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 08:44 |
| - | 31 | @ay<=1999 and gilbert.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:08 |
| - | 5 | @ay<=1999 and xing-guoqiang.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 10:59 |
| - | 692 | @ay<=1999 and 'capacitor' same 'lower electrode' with 'polysilicon'. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:18 |
| - | 1 | @ay<=1999 and 'capacitor' same 'lower electrode' with 'polysilicon' same 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:19 |
| - | 9 | @ay<=1999 and 'capacitor' same 'plug' with 'silicon' same 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:24 |

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| - | 29 | @ay<=1999 and 'contact plug' with 'silicon' same 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:25 |
| - | 21 | @ay<=1999 and 'contact plug' with 'silicon' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:37 |
| - | 48 | @ay<=1999 and 'capacitor' and 'doped' adj1 'silicon' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:38 |
| - | 76 | @ay<=1999 and 'electrode' and 'doped' adj1 'silicon' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:38 |
| - | 17 | @ay<=1999 and 'capacitor' with 'electrode' and 'doped' adj1 'silicon' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:51 |
| - | 33 | @ay<=1999 and 'electrode' same 'doped' adj1 'silicon' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:53 |
| - | 7 | @ay<=1999 and 'capacitor' with 'electrode' same 'doped' adj1 'silicon' with 'copper' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 09:52 |
| - | 0 | @ay<=1999 and ma-shawing.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 11:00 |
| - | 0 | @ay<=1999 and ma-shawing.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 11:00 |
| - | 0 | ma-shawing.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 11:00 |
| - | 1 | @ay<=1999 and ma-shawming.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 11:01 |
| - | 9 | ma-shawming.in. and 'ferroelectric' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 11:01 |
| - | 18 | @ad<=20010508 and 'amorphous BST' and 'perovskite' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/07/02 13:07 |